



DMP32D5SFB

#### 30V P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

V <sub>(BR)</sub> dss	R <sub>DS(ON)</sub> Max	<b>I<sub>D</sub> Max</b> @ T <sub>A</sub> = +25°C
-30V	2.4Ω @ V <sub>GS</sub> = -10V	-400mA
-307	$4\Omega @ V_{GS} = -4.5V$	-300mA

#### Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# Applications

- Load Switch
- **Portable Applications**
- **Power Management Functions**

## **Features**

- Low On-Resistance
- Ultra-Small Surfaced Mount Package
- **ESD** Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @

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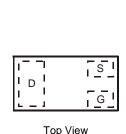
Weight: 0.001 grams (Approximate)





X1-DFN1006-3

**Bottom View** 



Gate Protection Diode Equivalent Circuit

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# Ordering Information (Note 4)

Part Number	Reel Size (inches)	Quantity per Reel
DMP32D5SFB-7B	7	10,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# Marking Information

Notes:



XH = Product Type Marking Code

Top View Bar Denotes Gate and Source Side



#### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note 5)	$V_{GS} = -10V$	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-400 -300	mA
Continuous Drain Current (Note 6)	V <sub>GS</sub> = -10V	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-500 -400	mA
Pulsed Drain Current (Note 5)			I <sub>DM</sub>	-1	А
Maximum Body Diode Continuous Current (Note 6)			ls	-800	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Tatal Dower Dissinction	(Note 5)	P	0.5	W	
Total Power Dissipation	(Note 6)	PD	1.2	VV	
Thermal Desistance, Junction to Ambient	(Note 5)	5	255	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ ext{ heta}JA}$	108		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Tes	t Condition
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	-	-	V	$V_{GS} = 0V, I_D$	= -1mA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	-1	μA	$V_{DS} = -30V, V_{DS} = -30V, V_{D$	$V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±10	μA	$V_{GS} = \pm 20V,$	$V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.3	-	-2.3	V	$V_{DS} = V_{GS}, I_{I}$	<sub>o</sub> = -250µA
Static Drain-Source On-Resistance			-	2.4	- Ω	$V_{GS} = -10V$ ,	I <sub>D</sub> = -200mA
	R <sub>DS(ON)</sub>	-		4		$V_{GS} = -4.5V$ ,	I <sub>D</sub> = -200mA
Diode Forward Voltage	V <sub>SD</sub>	-	0.8	1.2	V	$V_{GS} = 0V, I_{S} = -300mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	51	100	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	11	20	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	9	20	pF	1 = 1.010112	
Total Gate Charge	Qg	-	0.62	2	nC	$V_{GS} = -4.5V$	
Total Gate Charge	Qg	-	1.25	4	nC		$V_{DS} = -10V,$
Gate-Source Charge	Q <sub>gs</sub>	-	0.16	0.5	nC	V <sub>GS</sub> = -10V I <sub>D</sub> = -200mA	
Gate-Drain Charge	Q <sub>gd</sub>	-	0.21	0.5	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	-	4.3	10	ns		
Turn-On Rise Time	t <sub>R</sub>	-	7.7	15	ns	V <sub>DS</sub> = -15V, I <sub>D</sub> = -500mA	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	31.9	60	ns	V <sub>GS</sub> = -10V,	R <sub>G</sub> = 1Ω
Turn-Off Fall Time	t <sub>F</sub>	-	17.8	40	ns	7	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.

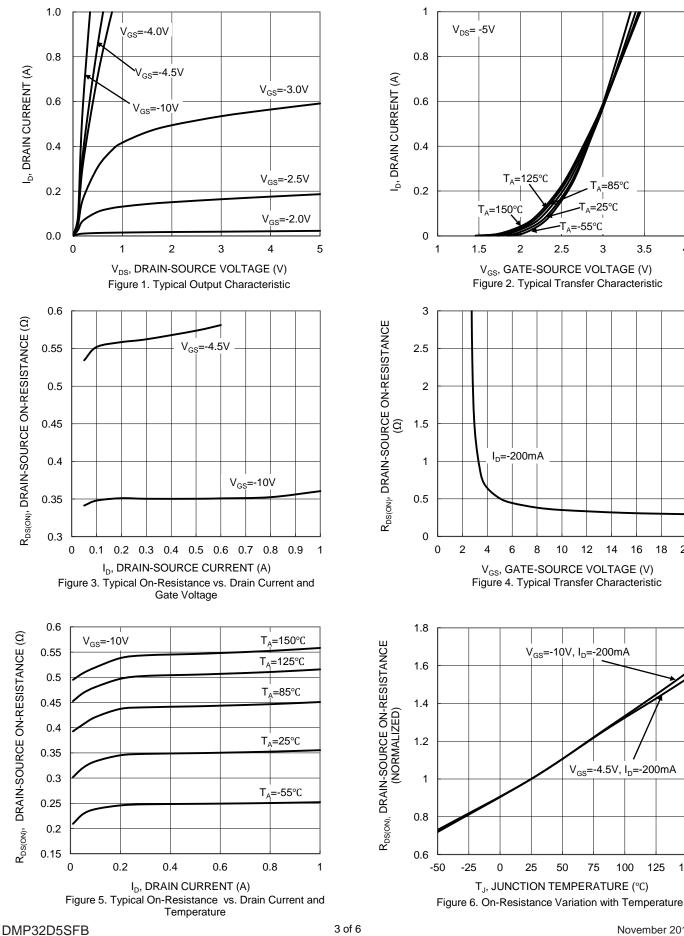


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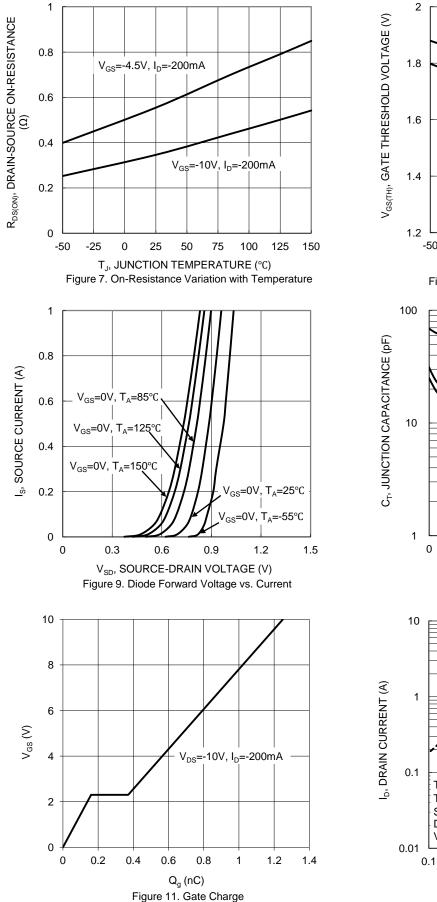
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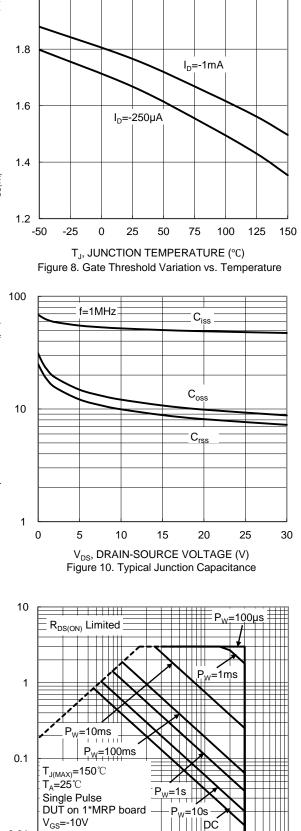
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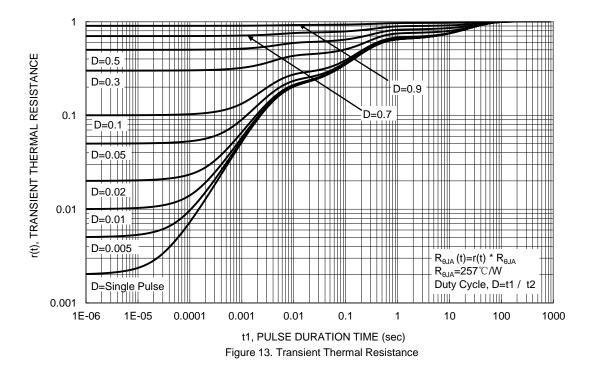
V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area

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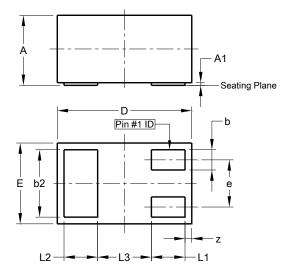
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# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

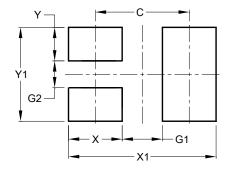


X1-DFN1006-3				
Dim	Min	Max	Тур	
Α	0.47	0.53	0.50	
A1	0.00	0.05	0.03	
b	0.10	0.20	0.15	
b2	0.45	0.55	0.50	
D	0.95	1.075	1.00	
Е	0.55	0.675	0.60	
е	-	-	0.35	
L1	0.20	0.30	0.25	
L2	0.20	0.30	0.25	
L3	-	-	0.40	
z	0.02	0.08	0.05	
All Dimensions in mm				



#### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70

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